

Anthony Aiello

List of Publications by Year in descending order

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12
papers

186
citations

1307366

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h-index

1199470

12
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12
all docs

12
docs citations

12
times ranked

252
citing authors

#	ARTICLE	IF	CITATIONS
1	III-nitride disk-in-nanowire 1.2-µm monolithic diode laser on (001)silicon. Applied Physics Letters, 2015, 107, .	1.5	37
2	Deep Ultraviolet Luminescence Due to Extreme Confinement in Monolayer GaN/Al(GaN) Nanowire and Planar Heterostructures. Nano Letters, 2019, 19, 7852-7858.	4.5	35
3	High-Gain Silicon-Based InGaN/GaN Dot-in-Nanowire Array Photodetector. ACS Photonics, 2019, 6, 1289-1294.	3.2	28
4	Removing Stripes, Scratches, and Curtaining with Nonrecoverable Compressed Sensing. Microscopy and Microanalysis, 2019, 25, 705-710.	0.2	21
5	Deep ultraviolet monolayer GaN/AlN disk-in-nanowire array photodiode on silicon. Applied Physics Letters, 2020, 116, .	1.5	18
6	Molecular beam epitaxy and characterization of Mg-doped GaN epilayers grown on Si (001) substrate through controlled nanowire coalescence. Journal of Crystal Growth, 2018, 498, 109-114.	0.7	14
7	InGaN/GaN Quantum Dot Light-Emitting Diodes on Silicon with Coalesced GaN Nanowire Buffer Layer. ACS Applied Nano Materials, 2021, 4, 1825-1830.	2.4	9
8	InGaN/GaN Quantum Dots on Silicon With Coalesced Nanowire Buffer Layers: A Potential Technology for Visible Silicon Photonics. IEEE Nanotechnology Magazine, 2020, 19, 571-574.	1.1	8
9	Optical and interface characteristics of Al _{0.56} Ga _{0.44} N/Al _{0.62} Ga _{0.38} N multiquantum wells with ~280 nm emission grown by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2019, 508, 66-71.	0.7	6
10	Wavelength tuning in the purple wavelengths using strain-controlled Al _x Ga _{1-x} N/GaN disk-in-wire structures. Applied Physics Letters, 2020, 116, 041102.	1.5	6
11	Removing Stripes, Scratches, and Curtaining with Non-Recoverable Compressed Sensing. Microscopy and Microanalysis, 2019, 25, 174-175.	0.2	2
12	Gradual Carrier Filling Effect in InGaN/GaN Quantum Dots: Femtosecond Carrier Kinetics with Sequential Two-Photon Absorption. ACS Applied Materials & Interfaces, 2021, 13, 45033-45039.	4.0	2